

Table of Contents

Preface

SmartSiC™ Substrates: A Boon to Drain Metallization Process

H. Cakmak, A. Thomas, S.A.H. Ratranaj, A.H.B.I.A. Yeo, S. Kumar, H. Xie, U. Chand, P. Vudumula, V.Q.G. Roth, L.K. Bera, N. Singh, S. Chung, L. Kabelaan, I. Radu and W. Schwarzenbach 1

Surface Structuring of Patterned 4H-SiC Surfaces Using a SiC/Si/SiC Sandwich Approach

Y. Jousseau, P. Kumar, M.E. Bathen, F. Cauwet, U. Grossner and G. Ferro 7

HYPREZ Wafering Solutions: A Novel Approach of SiC Wafering Solution

G. Lee, A. Hartmann and S. Kassir 13

Poly-SiC Characterization and Properties for SmartSiC™

H. Biard, A. Drouin, W. Schwarzenbach, K. Alassaad, L. Coeurdray, V. Chagneux, M. Coche, S. Ledrappier, S. Monnoye, H. Mank, S. Rouchier, T. Barge, D. Radisson, A. Moulin, S. Barbet, J. Widiez, S. Odoul and C. Maleville 21

Application of Advanced Characterization Techniques to SmartSiC™ Product for Substrate-Level Device Performance Optimization

A. Drouin, R.B. Simon, D. Radisson, W. Schwarzenbach, M. Zielinski, E. Guiot, E. Cela, A. Chappelle and H. Biard 27

A Novel Approach for Thin 4H-SiC Foil Realization Using Controlled Spalling from a 4H-SiC Wafer

S.N. Wahid, M. Leitgeb, G. Pfusterschmied and U. Schmid 35

High-Temperature Reorganization Behavior of Single-Crystalline Porous 4H-SiC Thin Foils

M. Perazzi, M. Leitgeb, A. Vengattoor Raghu, C. Zellner, R. Hahn, A. Kirnbauer, S. Schwarz, G. Pfusterschmied and U. Schmid 43

Dicing Process for 4H-SiC Wafers by Plasma Etching Using High-Pressure SF₆ Plasma with Metal Masks

Y. Sano, Y. Nakanishi, M. Oshima, S. Iden, J. Yamada, D. Toh and K. Yamauchi 51

Investigations on the Recovery of the Electrical Properties of Smart Cut™-Transferred SiC Thin Film Using SiC-on-Insulator Structures

G. Gelineau, C. Masante, E. Rolland, S. Barbet, L. Corbin, A. Papon, S. Caridroit, M. Delcroix, S. Huet, A. Moulin, V.S. Prudkovskiy, N. Troutot, S. Rouchier, L. Turchetti, K. Mony and J. Widiez 57

Demonstration of SiC-on-Insulator Substrate with Smart Cut™ Technology for Photonic Applications

S. Huet, S. Guerber, E. Rolland, B. Szelag, G. Gelineau, A. Moulin, V.S. Prudkovskiy, N. Troutot, C. Licitra, P. Gergaud, S. Barbet, M. Delcroix, S. Caridroit, V. Amalbert, C. Alonso-Ramos, D. Melati, S. Edmond, L. Vivien, K. Mony, G. Lapertot and J. Widiez 67

A Novel Contactless SiC Wafer Planarization Processing after Mechanical Slicing by Dynamic Thermal Annealing Processes

K. Toda, D. Kakutani, D. Dojima, Y. Nakajima, H. Mihara and T. Kaneko 77

Proposal of Damage-Free SiC Wafer Dicing Using Water Jet Guided Laser

S. Kadoya, S. Takahashi, M. Michihata, N. Ohtani, K. Abe and S. Arimura 85

In-Line Characterization of HPSI SiC Wafers Using High Resolution Surface Photovoltage Spectroscopy (HR-SPS)

T. Clausen, N. Schüler and K. Dornich 91

Characterization of Very Thin 3C-SiC Epilayers on Si

M. Zielinski, M. Bussel, M. Portail, A. Michon and Y. Cordier 97